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Faculty of Engineering

Spin Polarized Electronic Transport in Quantum Nanodevices

A thesis submitted in partial fulfillment for the award of the

Ph.D Degree in Engineering Physics

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STATEMENT

This thesis is submitted as partial fulfillment of Ph.D degree in Engineering Physics, Faculty of Engineering, Ain-Shams University.

The author carried out the work included in this thesis, and no part of it has been submitted for a degree or qualification at any other scientific entity.

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List of Publications

- [1] Ahmed S. Abdelrazek, Mohamed M. El-banna, and Adel H. Phillips, Quantum Spin Transport Characteristics in Graphene Field Effect Transistor. *Open Science Journal of Modern Physics*, **2(5)**, 55 (2015).
- [2] Ahmed S. Abdelrazek, Mohamed M. El-banna, and Adel H. Phillips, Coherent Manipulation of Spin Thermoelectric Dynamics in Graphene Nanodevice. *American Journal of Modern Physics and Application*, **2(4)**, 67 (2015).
- [3] Ahmed S. Abdelrazek, Mohamed M. El-banna, and Adel H. Phillips, Piezoelectric Effect on Spin Transport Characteristics of Ferromagnet/Semiconductor Junction, *Open Science Journal of Modern Physics*, **2(5)**, 72 (2015).
- [4] Ahmed S. Abdelrazek, Mohamed M. El-banna, and Adel H. Phillips, Spin Dependent Peltier Effect in Ferromagnetic Graphene/Superconducting Graphene Junction, *International Journal of Nanoscience and Nanoengineering*, **2(6)**, 36 (2015).
- [5] Ahmed S. Abdelrazek, Mohamed M. El-banna and Adel H. Phillips,. Photo-Spin Coherent Manipulation of Piezotronic Nanodevice, *Micro & Nano Letters*, 16 Sept.-2016,pp.1-5, doi: 10.1049/mnl.2016.0264.

ACKNOWLEDGEMENT.....	v
List of Publications.....	vi
CONTENTS.....	vii
List of Figures.....	ix
LIST OF SYMBOLS AND ABBREVIATIONS.....	xii
Thesis summary.....	xv
<u>Chapter I: Introduction</u>.....	1
I.1. Introductory Concepts.....	1
I.2. Literature survey.....	2
<u>CHAPTER II: THEORETICAL MODELS</u>.....	7
II.1 Spin Transport Characteristics of Diluted Ferromagnetic Semiconductor/ ZnO Semiconducting Curved Nanowire Junction.....	7
II.2 Quantum Spin Transport Characteristics in Graphene Field Effect Transistor.....	18
<u>CHAPTER III: RESULTS AND DISCUSSION</u>.....	26
III.1 First Model (Spin Transport Characteristics of Diluted Ferromagnetic Semiconductor/ ZnO Semiconducting curved nanowire Junction).....	26
III.2 Quantum Spin Transport Characteristics in Graphene Field Effect Transistor.....	38
<u>CHAPTER IV: CONCLUSION</u>.....	59
IV.1 The First Model of Nanodevice.....	59

IV.2 The Second Model of Nanodevice.....	60
References	62

Chapter I: Introduction

- Fig.I.1. Datta Spin Transistor [1].....1

CHAPTER II: THEORETICAL MODELS

- Figure-II.1. Schematic diagram of the suggested model.....8
- Figure-II.2. Schematic diagram of the suggested model..... 18

CHAPTER III: RESULTS AND DISCUSSION

- Figure-III.1. The variation of current, I , with the strain, η , at different values of source-drain voltage, V_{sd} , for both orientation of spin alignment.....28
- Figure-III.2. The behavior of the gauge factor, GF , with strain, η , at various values of source-drain voltage, V_{sd}29
- Figure-III.3. The behavior of Young's modulus, Y , with strain, η ,.....30
- Figure-III.4. The behavior of the Young's modulus, Y , with the giant magnetoresistance, GMR ,.....31
- Figure-III.5. The variation of the frequency associated with spin-orbit coupling, ω_{SOC} , with strain, η32
- Figure-III.6. The behavior of conductance with the strain at various values of gate voltage for different orientations of spin alignment.....33
- Figure-III.7. The behavior of (a) the spin polarization and (b) the giant magnetoresistance with the strain at various values of V_g ..35
- Figure-III.8. The behavior of the cutoff frequency with the strain at various values of the gate voltage for different orientations of spin alignment.....37

- Figure-III.9.The behavior of conductance, $G_{\uparrow\uparrow}$, with V_g at various frequencies of the ac-field.....39
- Figure-III.10.The behavior of the conductance, $G_{\uparrow\downarrow}$, with V_g at various values of frequencies of the ac-field.....40
- Figure-III.11. The behavior of the spin polarization, SP, with V_g at various frequencies of the induced ac-field.....41
- Figure-III.12.The behavior of the giant magnetoresistance, GMR, V_g at various frequencies of the induced ac-field.....42
- Figure-III.13. The behavior of the conductance, $G_{\uparrow\uparrow}$, with V_g at various values of the magnetic field.....43
- Figure-III.14.The behavior of the conductance, $G_{\uparrow\downarrow}$, with V_g , at various values of the magnetic field.....44
- Figure-III.15. The behavior of the spin polarization, SP, with gate voltage at various values of magnetic field.....45
- Figure-III.16. The behavior of the giant magnetresistance, GMR, with, V_g , at various values of the magnetic field.....45
- Figure-III.17. The behavior of the thermopower with, V_g , at various frequencies of the ac-field.....47
- Figure-III.18. The behavior of the thermal conductance with, V_g , at various frequencies of the induced ac-field.....48
- Figure-III.19. The behavior of the conductance with, V_g , at various frequencies of the ac-field.....49
- Figure-III.20. The behavior of the figure of merit with, V_g , at various frequencies of the induced ac-field.....50
- Figure-III.21.The variation of thermopower with the giant magnetoresistance.....51

- Figure-III.22. The behavior of thermopower with, V_g , at various magnitudes of magnetic fields.....52
- Figure-III.23. The behavior of electronic thermal conductance with, V_g , at various magnitudes of magnetic fields.....52
- Figure-III.24. The behavior of the conductance with, V_g , at various magnitudes magnetic fields.....53
- Figure-III.25. The variation of figure of merit with, V_g , at various magnitudes of magnetic fields.....54
- Figure-III.26. The variation of thermopower with the giant magnetoresistance.....54
- Figure-III.27. The behavior of the Peltier coefficient with , V_g , at various frequencies of the induced ac-field.....55
- Figure-III.28. The variation of the Peltier coefficient with the giant magnetoresistance.....56
- Figure-III.29. The behavior of the Peltier coefficient with, V_g , at various magnitudes of the magnetic fields.....57
- Figure-III.30. The variation of the Peltier coefficient with the giant magnetoresistance.....58

LIST OF SYMBOLS AND ABBREVIATIONS

- GMR: the giant magneto-resistance.
- E_g : The energy gap .
- \hbar : The reduced Planck's constant.
- \hat{H} : The Hamiltonian.
- V_g : The gate voltage.
- B : The applied magnetic field.
- V_{ac} : The amplitude of the AC-field.
- ω : the frequencies of the AC-field.
- V_{sd} : The bias voltage.
- m^* : The effective mass .
- ϕ_{SB} : The Schottky barrier height including the piezoelectric effect.
- σ : The Pauli matrices of spin.
- ψ : The components of the eigenfunction.
- μ_B : The Bohr magneton.
- h_0 : The exchange field energy of ferromagnetic leads.
- $\theta\omega$: The angle between two rectilinear part of the nanowire.
- α : The strength of the spin-orbit coupling.
- ξ : The precession angle of spin in the curved region of nanowire.
- ω_{SOC} : The frequency associated with spin-orbit coupling.
- J_n : The n^{th} order of Bessel functions of first kind.
- E'_F :The Fermi level in the presence of piezopotential.

- ρ_{piezo} :The density of polarization charges.
- w_{piezo} :The width of polarization charges
- GF :The gauge factor
- η :The strain
- Y_b :The Young's modulus of the bulk material.
- E_s : The surface energy.
- ν_r :The Poisson's ratio
- k_B : The Boltzmann's constant.
- T: The absolute temperature.
- G: The conductance.
- g: The Lande g-factor.
- SP: The spin polarization.
- f_T : The cutoff frequency.
- C: The gate capacitance with the nanowire.
- v_F : The Fermi velocity.
- Δ : The superconducting order parameter.
- T_c : The critical temperature of superconductor graphene.
- k_{\pm} :The wave vector of quasiparticles in the ferromagnetic graphene.
- k_{\pm}^s : The corresponding wave vector of quasiparticles in the superconducting graphene.
- E_{FI} :The Fermi-energy in the ferromagnetic graphene.
- θ : The Klein angle in ferromagnetic graphene (region I).
- S: The thermopower (Seebeck coefficient).
- K_e : The electronic thermal conductance.
- ZT: The thermoelectric figure of merit.
- Π : The Peltier coefficient.

- IT: Information technology.
- MBE: Molecular Beam Epitaxy.
- FM/SC: Ferromagnetic/Semiconductor.
- DMS: Diluted magnetic semiconductor.
- TM: Transition-metals.
- MTJ: Magnetic tunnel junction.
- Qubit: Quantum bit.
- LED: Light emitting diodes.
- PV: Photovoltaics.
- STM: Scanning tunneling microscopy.
- AFM: Atomic force microscopy.
- MTA: Micro-thermal analysis.
- SNOM: Scanning near-field optical microscopy.
- PZT: Lead zirconate titanate.
- MEMS: Micro-electromechanical system.
- Q1D: Quasi-one-dimensional.
- CMOS: Complementary metal oxide semiconductor.
- NW: Nanowire.
- FET: Field effect transistors.
- SWCNTFET: Single walled carbon nanotube field effect transistor.
- NEMS: Nanoelectromechanical system.
- QHE: Quantum Hall effect.
- NS: Normal metal/Superconducting metal.

THESIS SUMMERY

The Spintronics is the electronics that depend on the quantum concept of spin of electrons rather than their charge. The nanoelectronics which are based on spin require efficient ways to generate, manipulate and detect spin polarized currents and spin currents.

The present thesis is designed for investigating the quantum spin transport properties of two different types of nanostructures dominating nowadays nanoelectronics devices physics research.

First Model of Nanodevice:

Concerning this model we investigate the spin dynamics of nanoscale junction formed of diluted ferromagnetic semiconductor as two leads and a curved semiconducting nanowire. This nanowire is ZnO nanostructure, since it exhibits piezoelectric property. We shall study the spin transport characteristics of such junction by deducing the spin current for both different orientations of spin alignments by applying the effective mass approximation and the Floquet theory. The effect of strain, generated due bending the nanowire, on the spin current is investigated. Rashba spin-orbit interaction, the influence of the frequency of the induced ac-field and magnetic field are taken into consideration. Numerical calculations show that the spin current, for both orientations of spin alignment, varies with the induced strain strongly. This variation in the spin current with strain might be due to piezoelectric effect. Also, the strain gauge factor is calculated and it is noticed that this gauge factor varies with strain and attains a maximum value ≈ 973.4 at strain equals 0.1% and ≈ 961.9 at strain equals -0.1%. These large gauges factor may find applications in different fields of nanotechnology and bionanotechnology. It is noticed from calculations that the value of the frequency associated to spin-orbit coupling is affected by strain. The results appear that the spin transport